# 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a leadless ultra small DSN1006-2 (SOD993) Surface-Mounted Device (SMD) package.

### 2. Features and benefits

Average forward current: I<sub>F(AV)</sub> ≤ 1 A

Reverse voltage: V<sub>R</sub> ≤ 30 V

Low forward voltage, typical: V<sub>F</sub> = 415 mV
 Low reverse current, typical: I<sub>R</sub> = 300 μA

Package height typ. 270 µm

# 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Low power consumption applications
- Ultra high-speed switching
- · LED backlight for mobile application

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 145 °C; square wave	-	-	1	А
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C	-	-	30	V
V <sub>F</sub>	forward voltage	$I_F = 1 \text{ A}; t_p \le 300  \mu\text{s}; \delta \le 0.02 ;$ $T_j = 25 ^{\circ}\text{C}$	-	415	480	mV
I <sub>R</sub>	reverse current	$V_R = 20 \text{ V; } t_p \le 3 \text{ ms; } \delta \le 0.3 \text{ ;}$ $T_j = 25 \text{ °C}$	-	60	255	μΑ
		$V_R = 30 \text{ V; } t_p \le 3 \text{ ms; } \delta \le 0.3 \text{ ;}$ $T_j = 25 \text{ °C}$	-	300	1250	μΑ





 Table 2.
 Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		1 - 2
2	А	anode	1 2	sym001
			Transparent top view DSN1006-2 (SOD993)	

<sup>[1]</sup> The marking bar indicates the cathode.

# 5. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMEG3010AESB	DSN1006-2	DSN1006-2, leadless ultra small package; 2 terminals; body 1.0 x 0.6 x 0.27 mm	SOD993		

# 6. Marking

Table 4. Marking codes

Type number	Marking code
PMEG3010AESB	3A

# 7. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	30	V
I <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 140 °C; δ = 1		-	1.4	Α
I <sub>F(AV)</sub>	average forward current	$\bar{\delta}$ = 0.5 ; f = 20 kHz; $T_{amb} \leq$ 115 °C; square wave	[1]	-	1	A
		$\delta$ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 145 °C; square wave		-	1	A
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.25$		-	4	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	10	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	0.525	W
			[3]	-	1	W
			[1]	-	1.78	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm<sup>2</sup> each.

### 8. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1][2]	-	-	240	K/W
		[1][3]	-	-	125	K/W	
		[1][4]	-	-	70	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[5]	-	-	15	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm<sup>2</sup> each.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of anode tab.

PMEG3010AESB

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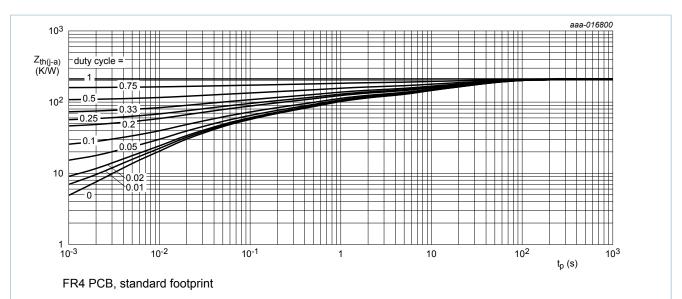


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

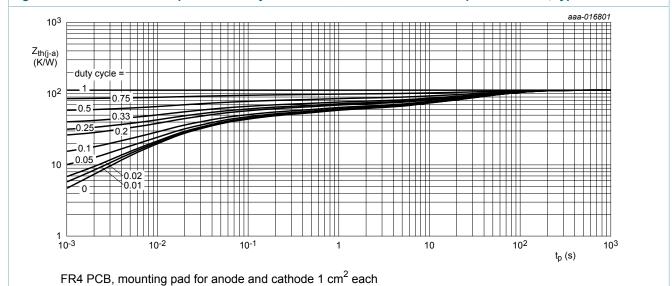
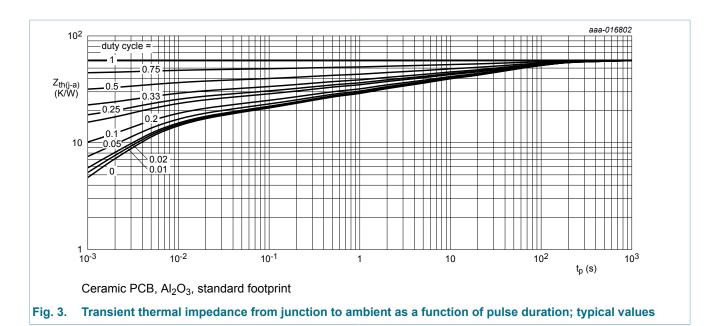


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



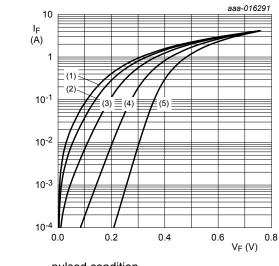
## 9. Characteristics

Table 7. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
reverse breakdown voltage	$I_R$ = 10 mA; $t_p$ = 300 µs; $\delta$ = 0.02 ; $T_j$ = 25 °C	30	-	-	V
forward voltage	$I_F$ = 1 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C	-	140	-	mV
	$I_F$ = 10 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C	-	200	-	mV
	$I_F$ = 100 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C	-	270	325	mV
	$I_F$ = 200 mA; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02 \ ;$ $T_j$ = 25 °C	-	300	-	mV
	$I_F$ = 500 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C	-	355	405	mV
	$I_F$ = 700 mA; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C	-	380	-	mV
	$I_F$ = 1 A; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_j$ = 25 °C	-	415	480	mV
reverse current	$V_R = 5 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ; T_j = 25 \text{ °C}$	-	13	-	μA
	$V_R = 10 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ;$ $T_j = 25 \text{ °C}$	-	22	90	μA
	$V_R = 20 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ;$ $T_i = 25 ^{\circ}\text{C}$	-	60	255	μA
	reverse breakdown voltage  forward voltage	$ \begin{array}{l} \text{reverse breakdown} \\ \text{voltage} \\ \end{array} \begin{array}{l} I_R = 10 \text{ mA; } t_p = 300  \mu \text{s; } \delta = 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \end{array} \\ \begin{array}{l} I_F = 1 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 100 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 200 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 200 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 500 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 700 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 1 \text{ A; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 1 \text{ A; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 1 \text{ A; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 1 \text{ A; } t_p \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ V; } t_p \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 20 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 25 \text{ °C} \\ \end{array} \\ \begin{array}{l} I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 10 \text{ V; } I_P \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ I_F = 10 \text{ V; } I_P \leq 3  $	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} \text{reverse breakdown} \\ \text{voltage} \\ \end{array} \begin{array}{c} I_R = 10 \text{ mA; } t_p = 300  \mu \text{s; } \delta = 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \end{array} \begin{array}{c} I_F = 1 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} I_F = 10 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \end{array} \begin{array}{c} - 200 \\ I_F = 100 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} I_F = 100 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \end{array} \begin{array}{c} - 270 \\ I_F = 200 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} I_F = 500 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \end{array} \begin{array}{c} - 355 \\ I_F = 700 \text{ mA; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} I_F = 1 \text{ A; } t_p \leq 300  \mu \text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \begin{array}{c} - 380 \\ \end{array} \\ \end{array} \\ \text{reverse current} \\ \begin{array}{c} V_R = 5 \text{ V; } t_p \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ; } T_j = 25 \text{ °C} \\ \end{array} \begin{array}{c} - 13 \\ \end{array} \\ V_R = 20 \text{ V; } t_p \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} - 22 \\ \end{array} \\ \end{array} \begin{array}{c} - 60 \\ \end{array} $	$ \begin{array}{c} \text{reverse breakdown} \\ \text{voltage} \\ \end{array} \begin{array}{c} I_R = 10 \text{ mA; } t_p = 300  \mu\text{s; } \delta = 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \end{array} \begin{array}{c} I_F = 1 \text{ mA; } t_p \leq 300  \mu\text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \hspace{0.5cm} I_F = 10 \text{ mA; } t_p \leq 300  \mu\text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \begin{array}{c} - 200 \\ I_F = 100 \text{ mA; } t_p \leq 300  \mu\text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \hspace{0.5cm} I_F = 100 \text{ mA; } t_p \leq 300  \mu\text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \begin{array}{c} - 270 \\ I_F = 200 \text{ mA; } t_p \leq 300  \mu\text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \hspace{0.5cm} I_F = 500 \text{ mA; } t_p \leq 300  \mu\text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \begin{array}{c} - 355 \\ I_F = 700 \text{ mA; } t_p \leq 300  \mu\text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \\ \hspace{0.5cm} I_F = 700 \text{ mA; } t_p \leq 300  \mu\text{s; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \begin{array}{c} - 380 \\ - 380 \\ \end{array} \begin{array}{c} - 380 \\ - 380 \\ \end{array} \\ \hspace{0.5cm} P = 10 \text{ V; } t_p \leq 3 \text{ ms; } \delta \leq 0.02 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \begin{array}{c} - 380 \\ - 380 \\ \end{array} \begin{array}{c} - 22 \\ 90 \\ \end{array} \\ \hspace{0.5cm} P = 10 \text{ V; } t_p \leq 3 \text{ ms; } \delta \leq 0.3 \text{ ;} \\ T_j = 25 \text{ °C} \\ \end{array} \begin{array}{c} - 355 \\ \end{array} \begin{array}{c} - 355 \\ \end{array} \begin{array}{c} - 355 \\ \end{array} \\ \hspace{0.5cm} - 355 \\ \end{array} \begin{array}{c} - 355 \\ \end{array} \\ \hspace{0.5cm} - 355 \\ \end{array} \begin{array}{c} - $

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_R = 30 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ;$ $T_j = 25 \text{ °C}$	-	300	1250	μΑ
C <sub>d</sub>	diode capacitance	$V_R = 1 \text{ V; } f = 1 \text{ MHz; } T_j = 25 ^{\circ}\text{C}$	-	86	-	pF
		$V_R = 10 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$	-	32	-	pF
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	3.5	-	ns



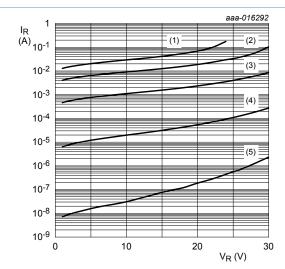


(1) 
$$T_j = 150 \,^{\circ}\text{C}$$
  
(2)  $T_i = 125 \,^{\circ}\text{C}$ 

(3) 
$$T_j = 85 \,^{\circ}\text{C}$$
  
(4)  $T_i = 25 \,^{\circ}\text{C}$ 

$$(5) T_i = -40 ^{\circ}C$$

Fig. 4. Forward current as a function of forward voltage; typical values



### pulsed condition

(1) 
$$T_i = 150 \, ^{\circ}C$$

(2) 
$$T_i = 125 \,^{\circ}C$$

(3) 
$$T_i = 85 \, ^{\circ}C$$

(4) 
$$T_i = 25 \, ^{\circ}C$$

(5) 
$$T_i = -40 \, ^{\circ}C$$

Fig. 5. Reverse current as a function of reverse voltage; typical values

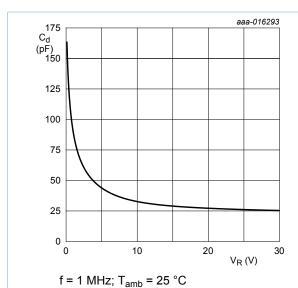
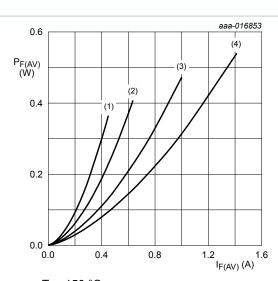


Fig. 6. Diode capacitance as a function of reverse voltage; typical values



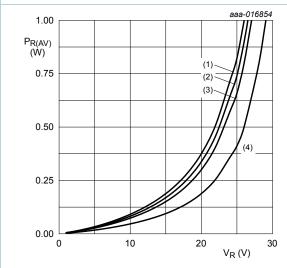
 $T_j = 150 \,^{\circ}\text{C}$ (1)  $\delta = 0.1$ 

 $(2) \delta = 0.2$ 

 $(3) \delta = 0.5$ 

 $(4) \delta = 1$ 

Fig. 7. Average forward power dissipation as a function of average forward current; typical values



 $T_j = 125 \,{}^{\circ}\text{C}$ 

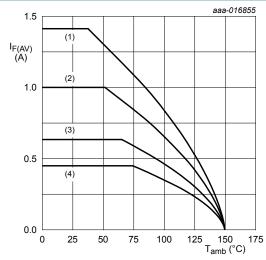
 $(1) \delta = 1$ 

 $(2) \delta = 0.9$ 

(3)  $\delta = 0.8$ 

(4)  $\delta = 0.5$ 

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T<sub>i</sub> = 150 °C

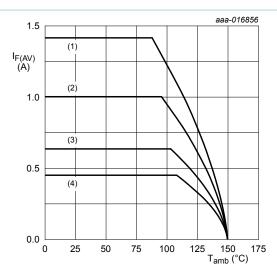
(1)  $\delta$  = 1; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for anode and cathode 1

cm<sup>2</sup> each

T<sub>j</sub> = 150 °C

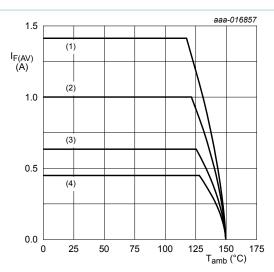
(1)  $\delta$  = 1; DC

(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

T<sub>i</sub> = 150 °C

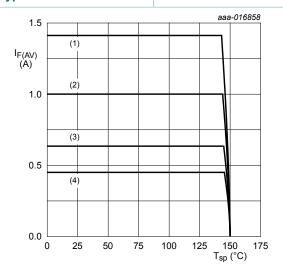
(1)  $\delta = 1$  (DC)

(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



T<sub>i</sub> = 150 °C

(1)  $\delta = 1$  (DC)

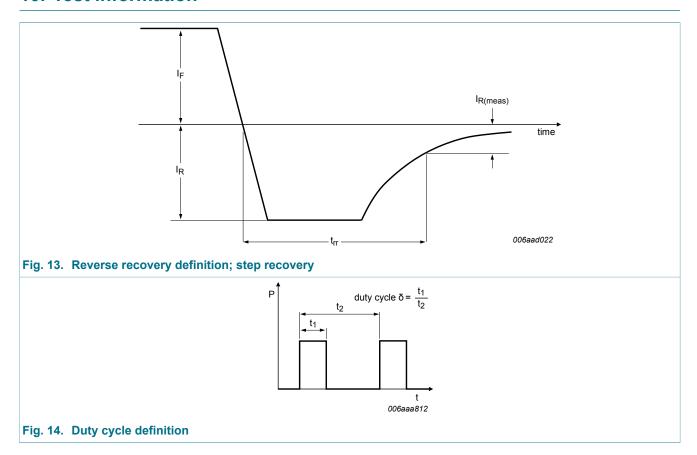
(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

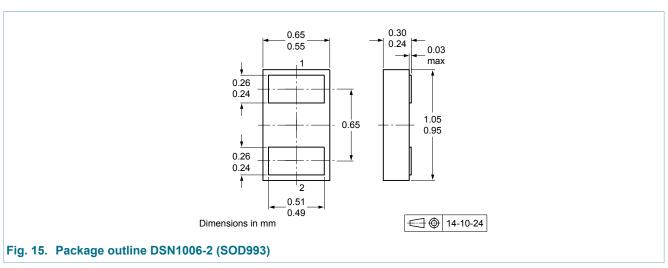
Fig. 12. Average forward current as a function of solder point temperature; typical values

## 10. Test information



The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

# 11. Package outline



PMEG3010AESB

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# 12. Soldering

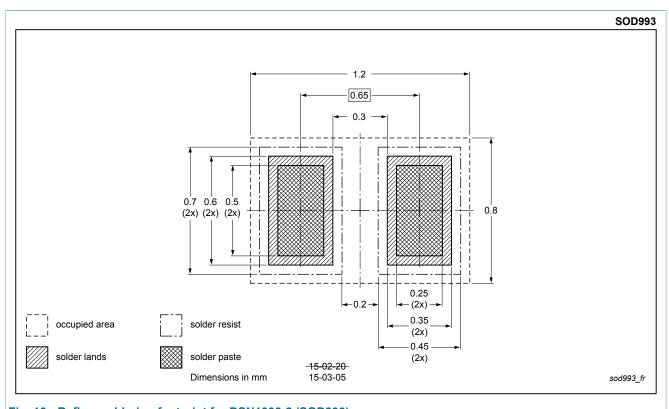


Fig. 16. Reflow soldering footprint for DSN1006-2 (SOD993)

# 13. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMEG3010AESB v.2	20150618	Product data sheet	-	PMEG3010AESB v.1	
Modifications:	Changed product status to "Product data sheet"				
PMEG3010AESB v.1	20150506	Preliminary data sheet	-	-	

## 14. Legal information

#### 14.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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